

PRELIMINARY - October 9, 2000

TEL:805-498-2111 FAX:805-498-3804 WEB:http://www.semtech.com

DESCRIPTION

The SC1110 is a low-cost, full featured, synchronous voltage-mode controller designed to generate termination voltage in double data rate (DDR) memory systems and other applications where wide data bus need to be actively terminated. Synchronous control of the MOSFET half bridge allows power flowing bi-directionally. The termination voltage can be tightly regulated to track the chipset voltage, i.e. to be exactly 50% of that at all times.

The SC1110 is ideal for low cost implementation of termination voltage supplies. SC1110 features include temperature compensated voltage reference, triangle wave oscillator and current sense comparator circuitry, and allows the use of inexpensive N-channel power switches.

The SC1110 operates at a fixed 250kHz, providing an optimum compromise between efficiency, transient performance, external component size, and cost.

FEATURES

- Generates termination voltages for active termination schemes
- 1% set point accuracy
- For $\pm 7A$ output current, transient regulation is better than $\pm 80mV$
- V_{REFIN} pin available
- Buffered V_{REFOUT} for system usage
- $R_{DS(on)}$ sensing for over current protection in hiccup mode
- Soft start and logic input enabling
- 250kHz switching for best transient and efficiency performance
- Gate drive capable for 0.5A sourcing and sinking

APPLICATIONS

- For DDR memory systems
- For active termination schemes in high speed logic systems

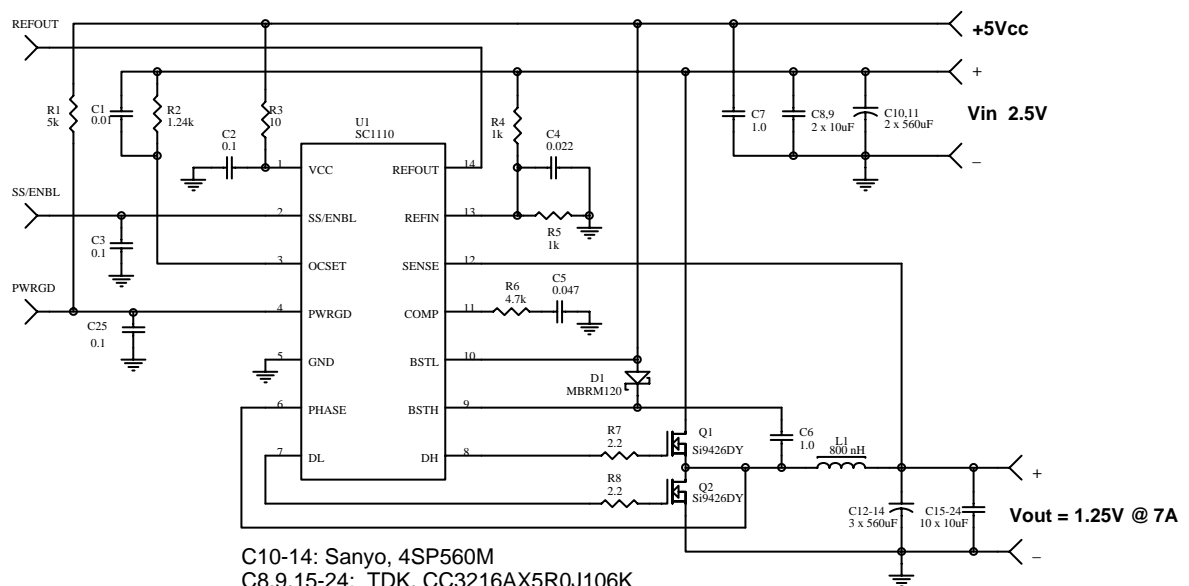
ORDERING INFORMATION

DEVICE ⁽¹⁾	PACKAGE	TEMP. RANGE (T _J)
SC1110CSTR	SO-14	0 - 125°C

Note:

(1) Only available in tape and reel packaging. A reel contains 2500 devices.

TYPICAL APPLICATION CIRCUIT



C10-14: Sanyo, 4SP560M
C8,9,15-24: TDK, CC3216AX5R0J106K
L1: Panasonic, ETQP6F0R8L or Falco, QPIP1205-809-3
Q1,Q2 options: Si9426DY, FDS6890A, IRF7401
D1: ON Semi (Motorola)

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ABSOLUTE MAXIMUM RATINGS

Parameter	Symbol	Maximum	Units
V _{CC} , BSTL to GND	V _{IN}	-0.5 to 14	V
PGND to GND		± 0.5	V
PHASE to GND		-0.5 to 18	V
BSTH to PHASE		14	V
Thermal Resistance Junction to Case	θ _{JC}	45	°C/W
Thermal Resistance Junction to Ambient	θ _{JA}	115	°C/W
Operating Temperature Range	T _A	0 to 70	°C
Storage Temperature Range	T _{STG}	-65 to +150	°C
Lead Temperature (Soldering) 10 sec	T _{LEAD}	300	°C

ELECTRICAL CHARACTERISTICS

Unless specified: V_{CC} = 4.75V to 12.6V; GND = PGND = 0V; FB = V_O; V_{BSTL} = 12V; V_{BSTH-PHASE} = 12V; T_J = 25°C

PARAMETER	CONDITIONS	MIN	TYP	MAX	UNITS
POWER SUPPLY					
Supply Voltage	V _{CC}	4.4		12.6	V
Supply Current	EN = V _{CC}		8		mA
Line Regulation	V _{IN} = 2.5 ± 0.5V, V _O = V _{IN} /2 @ 0A		0.5		%
UNDER VOLTAGE LOCKOUT					
Turn-On Threshold		TBD	4.2	TBD	V
Turn-Off Threshold		TBD	4.0	TBD	V
ERROR AMPLIFIER					
Transconductance			2		mS
Open Loop DC Gain			50		dB
Bandwidth -3dB			500		kHz
COMP Source Capability			±250		μA
Input Bias			5	8	μA
OSCILLATOR					
Oscillator Frequency		225	250	275	kHz
Oscillator Max Duty Cycle		90	95		%
Ramp Height			1		V
TIMING					
Minimum Off-Time			100		ns
Dead Time		80			ns

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ELECTRICAL CHARACTERISTICS

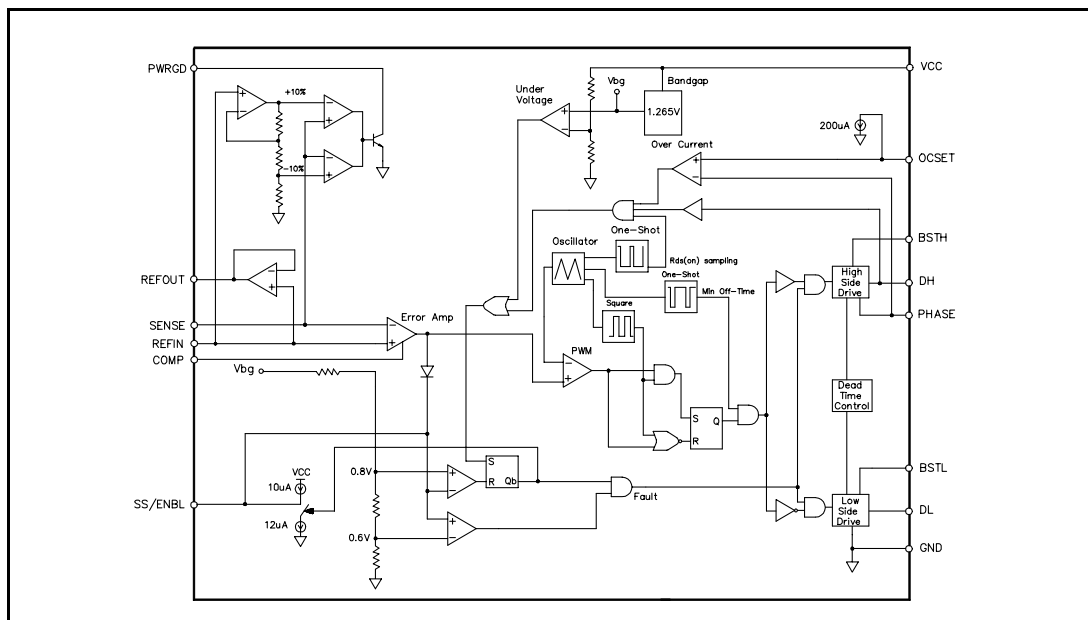
Unless specified: $V_{CC} = 4.75V$ to $12.6V$; $GND = PGND = 0V$; $FB = V_O$; $V_{BSTL} = 12V$; $V_{BSTH-PHASE} = 12V$; $T_J = 25^\circ C$

PARAMETER	CONDITIONS	MIN	TYP	MAX	UNITS
MOSFET DRIVERS					
Peak DH Sink/Source Current	BSTH - DH = 4.5V, DH - PHASE = 3.0V DH - PHASE = 1.5V	0.5			A
		0.1			
Peak DL Sink/Source Current	BSTL - DL = 4.5V, DL - GND = 3.0V DL - GND = 1.5V	0.5			A
		0.1			
PROTECTION					
Over Current Set Isource	V _{OCSET} = 4.5V	180	200	220	μA
SOFT START					
Charge Current	V _{SS} = 1.5V		10		μA
Discharge Current	V _{SS} = 1.5V		2		μA
POWER GOOD					
Upper Threshold			112		%
Lower Threshold			88		%
PWRGD Voltage Low	I _{PWRGD} = 2mA			0.5	V
REFERENCE					
REFOUT Source Current			3		mA
Input Bias			5	8	μA

NOTE:

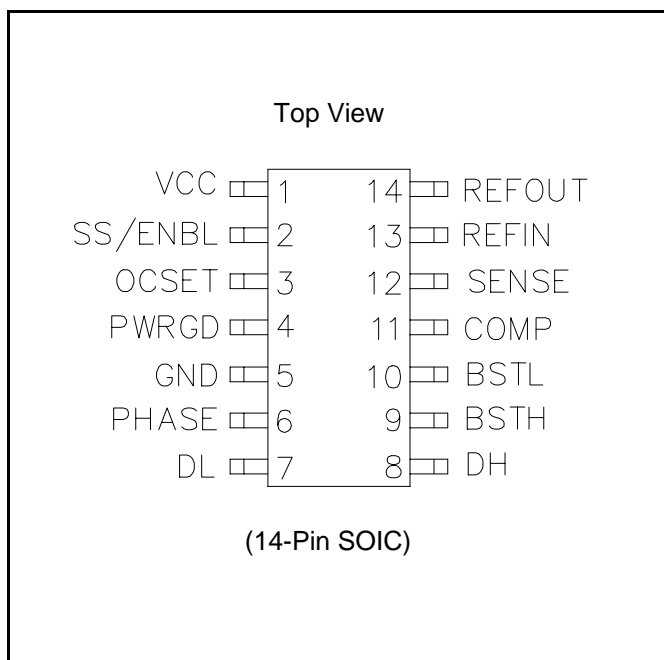
(1) Specification refers to application circuit (Figure 1.).

BLOCK DIAGRAM



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PIN CONFIGURATION



PIN DESCRIPTION

Pin #	Pin Name	Pin Function
1	VCC	Chip supply voltage.
2	SS/ENBL	Soft start/Enable.
3	OCSET	Current limit set point.
4	PWRGD	Logic high indicates correct output.
5	GND	Ground.
6	PHASE	Phase node connection between MOSFET's.
7	DL	Low side driver output.
8	DH	High side driver output.
9	BSTH	High side drive supply.
10	BSTL	Low side drive supply.
11	COMP	Error amplifier output, compensation.
12	SENSE	Error amplifier negative input.
13	REFIN	Error amplifier positive input.
14	REFOUT	Buffered reference voltage.

NOTE:

(1) All logic level inputs and outputs are open collector TTL compatible.

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THEORY OF OPERATION

Synchronous Buck Converter

$V_{\text{TERMINATION}}$ power is provided by a synchronous, voltage-mode pulse width modulated (PWM) controller. This section has all the features required to build a high efficiency synchronous buck converter for termination of power application.

The output voltage of the synchronous converter is set and controlled by the output of the error amplifier. The resistive divider generates reference voltage for the error amplifier from an external chipset voltage which is usually 2.5V. The inverting input of the error amplifier receives its voltage from the SENSE pin.

The internal oscillator uses an on-chip capacitor and trimmed precision current sources to set the oscillation frequency to 250kHz. The triangular output of the oscillator sets the reference voltage at the inverting input of the PWM comparator. The non-inverting input of the comparator receives its input voltage from the error amplifier. When the oscillator output voltage drops below the error amplifier output voltage, the comparator output goes high. This pulls DL low, turning off the low-side FET, and DH is pulled high, turning on the high-side FET (once the cross-current control allows it). When the oscillator voltage rises back above the error amplifier output voltage, the comparator output goes low. This pulls DH low, turning off the high-side FET, and DL is pulled high, turning on the low-side FET (once the cross-current control allows it).

As SENSE increases, the output voltage of the error amplifier decreases. This causes a reduction in the on-time of the high-side MOSFET connected to DH, hence lowering the output voltage.

Under Voltage Lockout

The under voltage lockout circuit of the SC1110 assures that both the high-side MOSFET driver outputs remain in the off state whenever the supply voltage drops below set parameters. Lockout occurs if V_{CC} falls below 4.0V. Normal operation resumes once V_{CC} rises above 4.2V.

Soft Start

Initially, SS/ENABLE sources 10 μ A of current to charge an external capacitor. The outputs of the error amplifiers are clamped to a voltage proportional to the voltage on SS/ENABLE. This limits the on-time of the high-side MOSFETs, thus leading to a controlled ramp-up of the output voltages.

$R_{\text{DS(ON)}}$ Current Limiting

The current limit threshold is set by connecting an external resistor from the V_{CC} supply to OCSET. The voltage drop across this resistor is due to the 200 μ A internal sink sets the voltage at the pin. This voltage is compared to the voltage at the PHASE node. This comparison is made only when the high-side drive is high to avoid false current limit triggering due to uncontributing measurements from the MOSFET's off-voltage. When the voltage at PHASE is less than the voltage at OCSET, an overcurrent condition occurs and the soft start cycle is initiated. The synchronous switcher turns off and SS/ENABLE starts to sink 2 μ A. When SS/ENABLE reaches 0.8V, it then starts to source 10 μ A and a new cycle begins.

Hiccup Mode

During power up, the SS/ENABLE pin is internally pulled low until V_{CC} reaches the undervoltage lockout level of 4.2V. Once V_{CC} has reached 4.2V, the SS/ENABLE pin is released and begins to source 10 μ A of current to the external soft-start capacitor. As the soft-start voltage rises, the output of the internal error amplifier is clamped to this voltage. When the error signal reaches the level of the internal triangular oscillator, which swings from 1V to 2V at a fixed frequency of 250 kHz, switching occurs. As the error signal crosses over the oscillator signal, the duty cycle of the PWM signal continues to increase until the output comes into regulation. If an over-current condition has not occurred the soft-start voltage will continue to rise and level off at about 2.2V.

An over-current condition occurs when the high-side drive is turned on, but the PHASE node does not reach the voltage level set at the OCSET pin. The PHASE node is sampled only once per cycle during the valley of the triangular oscillator. Once an over-current occurs, both the high-side and low-side drivers turn off and the SS/ENABLE pin begins to sink 2 μ A. The soft-start voltage will begin to decrease as the 2 μ A of current discharges the external capacitor. When the soft-start voltage reaches 0.8V, the SS/ENABLE pin will begin to source 10 μ A and begin to charge the external capacitor causing the soft-start voltage to rise again. Again, when the soft-start voltage reaches the level of the internal oscillator, switching will occur.

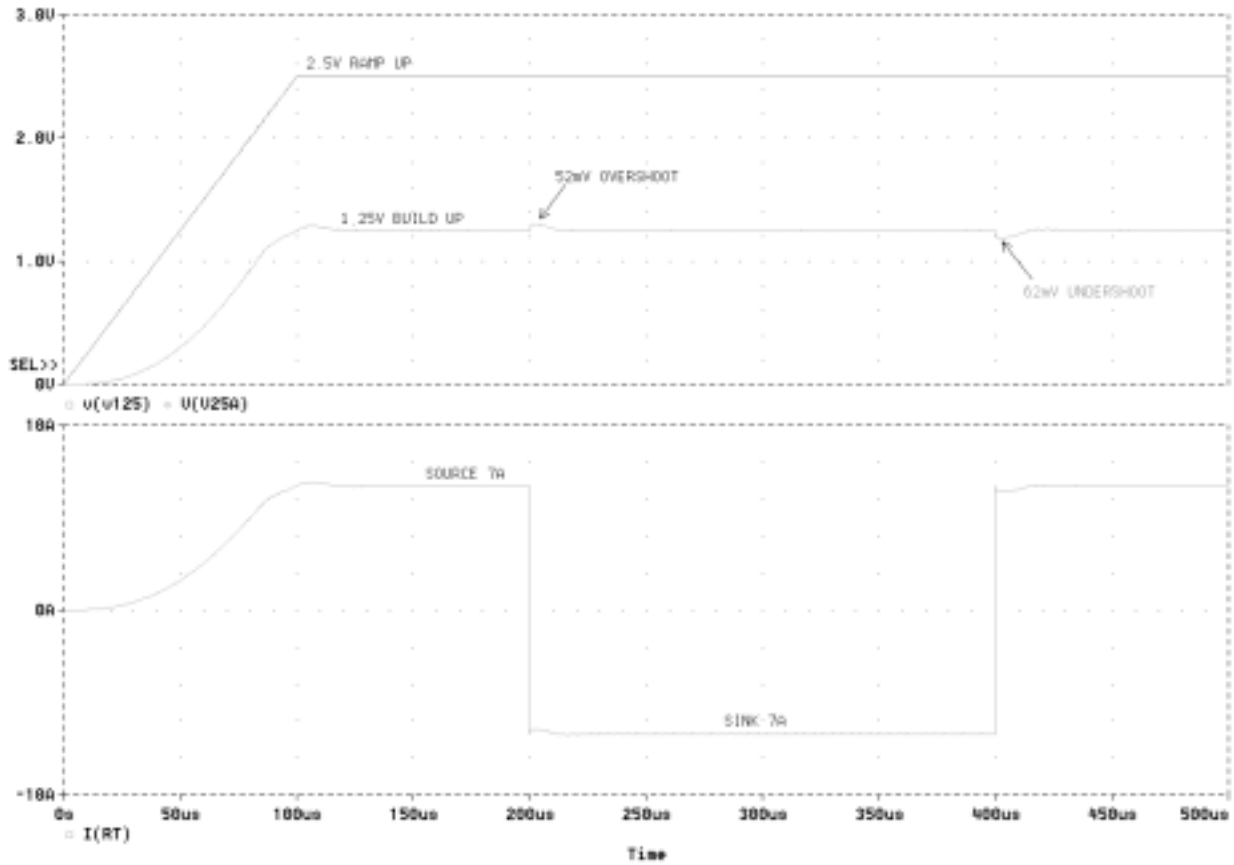
If the over-current condition is no longer present, normal operation will continue. If the over-current condition is still present, the SS/ENABLE pin will again begin to sink 2 μ A. This cycle will continue indefinitely until the over-current condition is removed.



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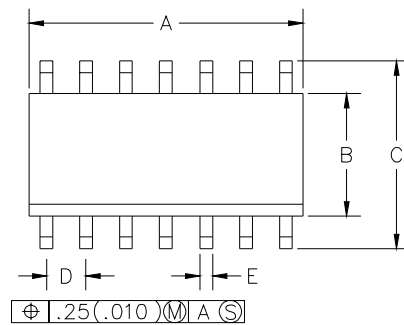
SIMULATION WAVEFORMS

2.5V and 1.25V ramp up

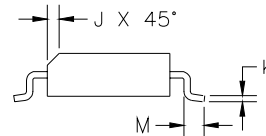
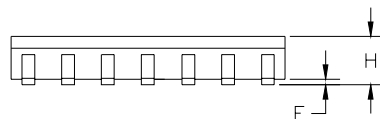


Output current of the VTT supply

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OUTLINE DRAWING SO-14


DIM ^N	DIMENSIONS				NOTE
	INCHES		MM		
A	.337	.344	8.55	8.75	2
B	.150	.158	3.80	4.00	3
C	.228	.244	5.80	6.20	
D	.050	BSC	1.27	BSC	
E	.013	.020	0.33	0.51	
F	.004	.010	0.10	0.25	
H	.053	.069	1.35	1.75	
J	.010	.020	0.25	0.50	
K	.007	.010	.19	.25	
M	.016	.050	0.40	1.27	



- ☐ DIMENSION "B" DOES NOT INCLUDE INTER-LEAD FLASH OR PROTRUSIONS. INTER-LEAD FLASH AND PROTRUSIONS SHALL NOT EXCEED .25 mm (.010") PER SIDE.
- ☐ DIMENSION "A" DOES NOT INCLUDE MOLD FLASH, PROTRUSIONS OR GATE BURRS. MOLD FLASH, PROTRUSIONS AND GATE BURRS SHALL NOT EXCEED .15 mm (.010") PER SIDE.
- ☐ CONTROLLING DIMENSION : MILLIMETER

ECN00-1363